L Number	Hits	Search Text	DB	Time stamp
-	110	vacancy near2 dominat\$ and silicon .	USPAT; US-PGPUB; EPO; JPO;	2004/02/20 09:20
-	33	vacancy near2 dominat\$ and silicon and @py<2002	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 10:19
-	2	20020121238.pn.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 09:22
-	1	0022197.pn.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 09:25
_	58	"0022197"	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 09:33
_	16-	vacancy near2 dominat\$ near20 segment and silicon	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 09:37
_	21	idEAL near2 OXYGEN near2 PRECIPITATING near2 SILICON	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 10:08
_	1 9	vacancy near2 dominat\$ and void near2 density	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 10:09
-	. 1 660	void near2 density	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 10:09
-	* 7	void near2 density and silicon adj ingot	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 10:09
_	. 8	void near2 density and silicon near2 ingot	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20
_	1	void near2 density and memc.as.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 10:12
-	53	residual near5 vacancy	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 10:12
-	17	residual near5 vacancy and silicon near10 (wafer or ingot)	DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/20 10:12

_	101	vacancy near2 dominat\$ and silicon near10	USPAT;	2004/02/20
		(wafer or ingot)	US-PGPUB;	10:19
			EPO; JPO;	
			DERWENT; IBM TDB	
	1	(vacancy near2 dominat\$ and silicon	USPAT;	2004/02/20
-	1	near10 (wafer or ingot)) and void near4	US-PGPUB;	10:19
		density	EPO; JPO;	10.13
		density	DERWENT;	
			IBM TDB	
<u>-</u>	39	(vacancy near2 dominat\$ and silicon	USPĀT;	2004/02/20
		near10 (wafer or ingot)) and void	US-PGPUB;	10:20
		•	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	41		USPAT;	2004/02/20
]		near10 (wafer or ingot)) and nitrogen	US-PGPUB;	10:21
1			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	2004/02/20
_	3		USPAT; US-PGPUB;	2004/02/20
		near10 (wafer or ingot)) and nitrogen near10 less	EPO; JPO;	10.22
		Hearin Tess	DERWENT;	
			IBM TDB	
_	22	(vacancy near2 dominat\$ and silicon	USPAT;	2004/02/20
		near10 (wafer or ingot)) and nitrogen	US-PGPUB;	10:27
1		near10 (content or concentration or	EPO; JPO;	
		amount)	DERWENT;	
ł		,	IBM TDB	Ì
_	395		USPAT;	2004/02/20
		nitrogen near10 (content or concentration	US-PGPUB;	10:28
		or amount) near10 less	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/00/00
-	34		USPAT;	2004/02/20
		nitrogen near5 (content or concentration	US-PGPUB; EPO; JPO;	10:32
		or amount) near5 less	DERWENT;	
	:		IBM TDB	
l _	9	silicon near2 (wafer or ingot) same "13	USPAT;	2004/02/20
		ppma"	US-PGPUB;	10:33
		ppma	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	157	vacancy same void and (si or silicon)	USPĀT;	2004/02/20
1		near10 (wafer or ingot)	US-PGPUB;	11:05
[EPO; JPO;	
			DERWENT;	
		1	IBM_TDB	2004/02/20
-	123		USPAT;	2004/02/20 11:06
1		near10 (wafer or ingot)	US-PGPUB; EPO; JPO;	11.00
			DERWENT;	
			IBM TDB	
_	34	vacancy near10 void near10 (density or	USPAT;	2004/02/20
		content or concentration) and (si or	US-PGPUB;	11:17
		silicon) near10 (wafer or ingot)	EPO; JPO;	
		,	DERWENT;	
			IBM_TDB	
-	172	vacancy near10 agglomerat\$ and (silicon	USPĀT;	2004/02/20
		or si) near2 (ingot or wafer)	US-PGPUB;	11:17
1			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	2004/02/20
-	90		USPAT;	2004/02/20 11:18
		or si) near2 (ingot or wafer) and vacancy near3 dominat\$	US-PGPUB; EPO; JPO;	11.10
		Inears dominars	DERWENT;	
			IBM TDB	
1	1	L	+	l

	•			
_	79	<pre>vacancy near10 agglomerat\$ same dominat\$ and (silicon or si) near2 (ingot or wafer)</pre>	USPAT; US-PGPUB; EPO; JPO;	2004/02/20 11:18
			DERWENT; IBM_TDB	
-	68	<pre>vacancy near10 agglomerat\$ near10 dominat\$ and (silicon or si) near2 (ingot or wafer)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/20 11:29
-	34	<pre>vacancy near3 agglomerat\$ near10 dominat\$ and (silicon or si) near2 (ingot or wafer)</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 11:49
-	379748	low near5 oxygen near10 ppma same fault and (si or silicon) nera3 (wafer or	DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/02/20 11:50
		ingot)	EPO; JPO; DERWENT; IBM TDB	
_	27	low near5 oxygen near10 ppma same fault and (si or silicon) near3 (wafer or ingot)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/20 12:00
_	53	residual near5 vacancy	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 12:00
_	19	residual near5 vacancy and (si or silicon) near4 (ingot or wafer)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 12:04
_	2	"2000183068"	DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/02/20
-	47	\$2control\$4 near10 precipitat\$ same vacancy and (si or silicon) near2 (ingot	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/02/20 12:59
		or wafer)	EPO; JPO; DERWENT; IBM TDB	
-	71	"0014776"	USPAT; US-PGPUB; EPO; JPO;	2004/02/20 13:05
-	3	agglomerat\$ near3 vacancy near10 radius near10 nm	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20
_	5	agglomerat\$ near3 vacancy near10 nm	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20
	83	agglomerat\$ near3 vacancy near15	DERWENT; IBM_TDB USPAT;	2004/02/20
	03	(diameter or radius or width or size)	US-PGPUB; EPO; JPO; DERWENT;	13:13
-,	79	agglomerat\$ near3 vacancy near10 (diameter or radius or width or size)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/20 13:35
			DERWENT; IBM_TDB	

	49	agglomerat\$ near3 vacancy near10 integ\$5	USPAT;	2004/02/20
_	4.5	aggiomeracy means themself means.	US-PGPUB;	13:41
			EPO; JPO;	1
•			DERWENT;	
			IBM TDB	
l _	83	agglomerat\$ near3 vacancy near10 (size or	USPAT;	2004/02/20
		density)	US-PGPUB;	13:53
			EPO; JPO;	1
	!		DERWENT;	
			IBM_TDB	
_	32	agglomerat\$ near3 vacancy near10 size	USPAT;	2004/02/20
		4499	US-PGPUB;	13:55
			EPO; JPO;	
			DERWENT;	
	i		IBM_TDB	
_	l 0	6146459.pn. and agglomer\$ near3 size	USPAT;	2004/02/20
			US-PGPUB;	13:56
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	2	6146459.pn. and agglomer\$	USPAT;	2004/02/20
	. 8	•	US-PGPUB;	14:51
	4		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	45	residual near4 vacancy	USPAT;	2004/02/20
1			US-PGPUB;	14:52
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

L Number	Hits	Search Text	DB ·	Time stamp
1	879	428/64.1.ccls.	USPAT;	2004/03/05 15:15
2	0	428/64.1.ccls. and void adj density	US-PGPUB USPAT;	2004/03/05 15:15
3	118	428/64.1.ccls. and defects	US-PGPUB USPAT; US-PGPUB	2004/03/05 15:15
4	890	428/64.4.ccls.	USPAT; US-PGPUB	2004/03/05 15:16
5	7	428/64.4.ccls. and silicon adj wafers	USPAT; US-PGPUB	2004/03/05 15:16
6 .	428	117/13.ccls.	USPAT; US-PGPUB	2004/03/05 15:16
7	190	117/13.ccls. and ingot	USPAT; US-PGPUB	2004/03/05 15:16
8	133	(117/13.ccls. and ingot) and defects	USPAT; US-PGPUB	2004/03/05 15:18
9	122	117/20.ccls.	USPAT; US-PGPUB	2004/03/05 15:18
10	554	117/932.ccls.	USPAT; US-PGPUB	2004/03/05 15:18
11	. 26	117/932.ccls. and voids	USPAT; US-PGPUB	2004/03/05 15:18
_	2	average adj void adj density	USPAT; US-PGPUB	2004/03/04 17:14
-	65	density same agglomerated adj defects	USPAT; US-PGPUB	2004/03/04 17:48
_	66,	(void adj density) not (density same agglomerated adj defects)	USPAT; US-PGPUB	2004/03/04 17:19
_	68	density same agglomerated adj defects	USPAT; US-PGPUB;	2004/03/04 17:23
-	38	density near agglomerated adj defects	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 17:23
_	0	(density near agglomerated adj defects) not (density same agglomerated adj defects)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 17:23
-	1929	density same agglomerated	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/04 17:25
	0	"118" near defects	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/04 17:24
	217	(density same agglomerated) and defects	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/04 17:26
-	68	density same agglomerated near defects	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/04 17:25
-	. 0	(density same agglomerated near defects) not (density same agglomerated adj defects)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/04 17:25

-	80	agglomerated adj defects	USPAT;	2004/03/04 17:26
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		. · · · · · · · · · · · · · · · · · · ·	IBM TDB	1
-	77	(agglomerated adj defects) and density	USPAT;	2004/03/04 17:26
			US-PGPUB;	
		·	EPO; JPO;	
			DERWENT;	
	,		IBM_TDB	
 .	9	((aggromoratora daj dorotor, dia denorej,	USPAT;	2004/03/04 17:27
		not (density same agglomerated adj	US-PGPUB;	
		defects)	EPO; JPO;	
		.	DERWENT;	′
			IBM TDB	
_	67	void adj density	USPĀT;	2004/03/04 17:42
			US-PGPUB	
-	0	high adj denstiy same agglomerated adj	USPAT;	2004/03/04 17:49
		defects	US-PGPUB	
-	0	high adj denstiy same vacancy adj defects	USPAT;	2004/03/04 17:49
			US-PGPUB	
-	0	high adj denstiy same vacancy	USPAT;	2004/03/04 17:49
			US-PGPUB	
_	628	void adj size	USPAT;	2004/03/05 10:59
-			US-PGPUB	
-	1	void adj size near radius	USPAT;	2004/03/05 10:59
		-	US-PGPUB	
_	31	void adj radius	USPAT;	2004/03/05 11:00
			US-PGPUB	
_	1	(void adj size) and agglomerated adj	USPAT;	2004/03/05 11:00
		defects	US-PGPUB	
<u> </u>	7	(void adj size) and defects and vacancy	USPAT;	2004/03/05 11:12
			US-PGPUB	
-	994	defect adj size	USPAT;	2004/03/05 11:23
			US-PGPUB	
-	1218	small adj voids	USPAT;	2004/03/05 13:11
		- · · · · · · · · · · · · · · · · · · ·	US-PGPUB	
-	40	(small adj voids) and silicon adj wafer	USPAT;	2004/03/05 15:15
			US-PGPUB	
-	5	((small adj voids) and silicon adj wafer)	USPAT;	2004/03/05 13:15
		and void near size	US-PGPUB	